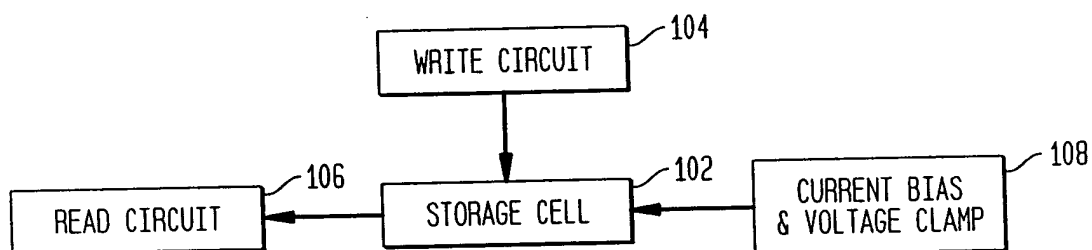
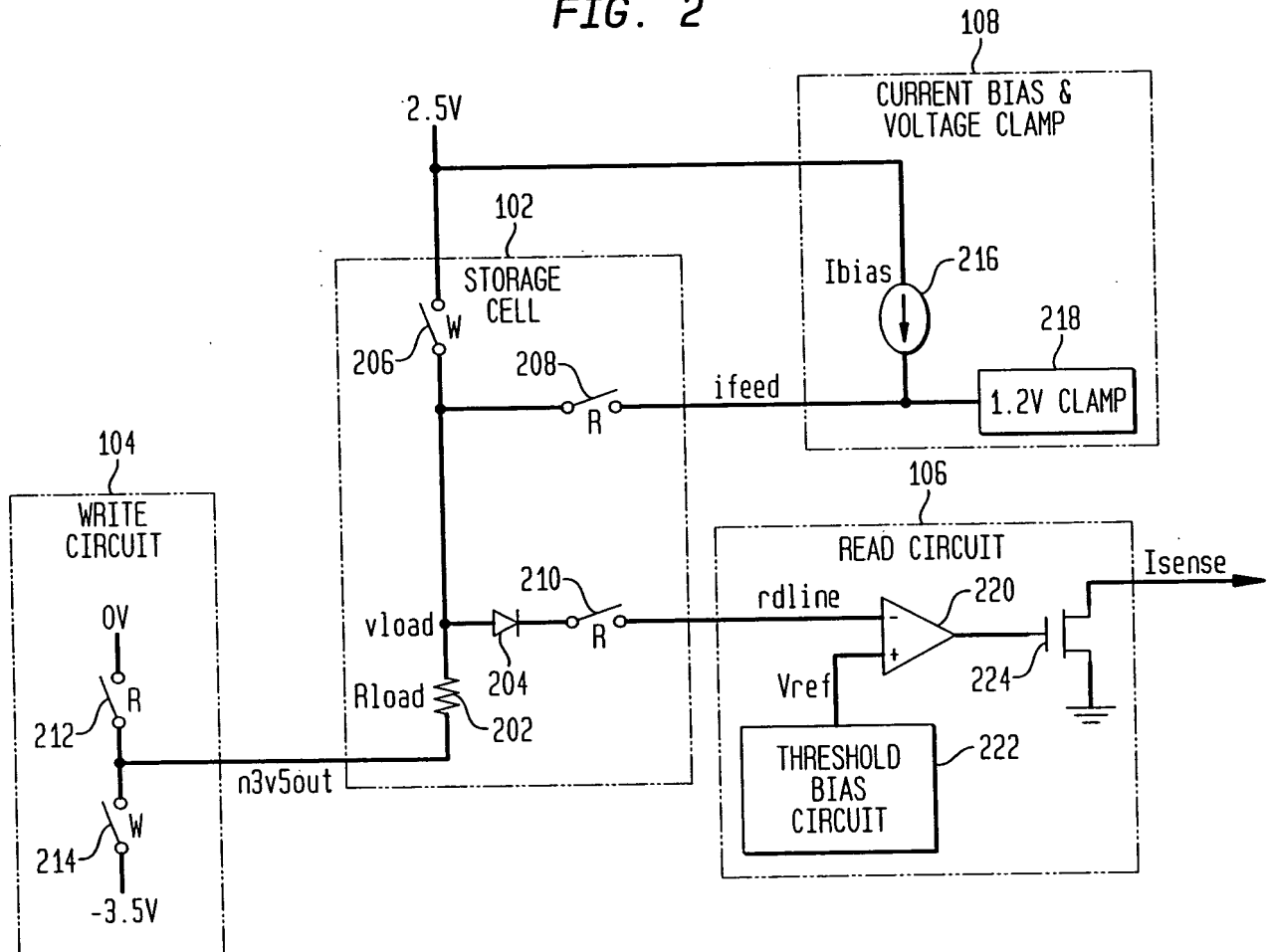


FIG. 1

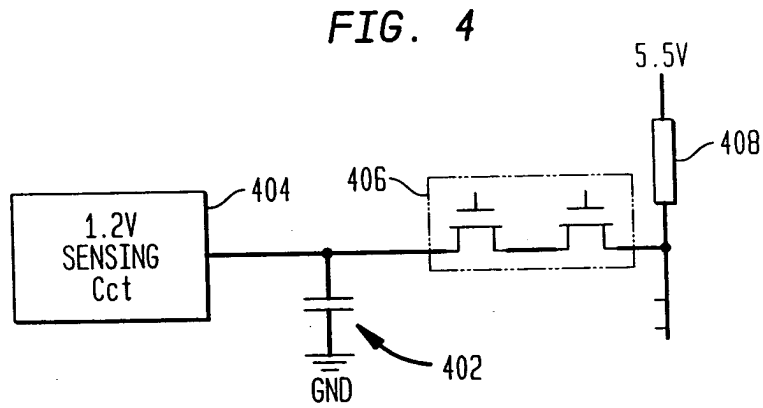
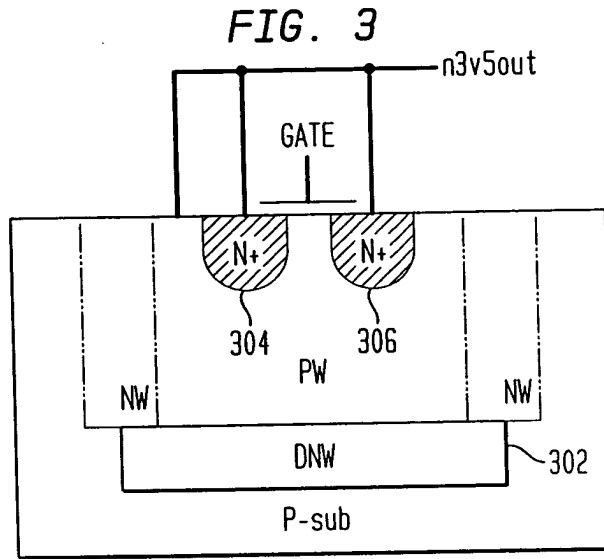


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 Inventors: Chen *et al.*; Tel.: (202) 371-2600
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 Memory Through Direct-Tunneling Oxide Breakdown

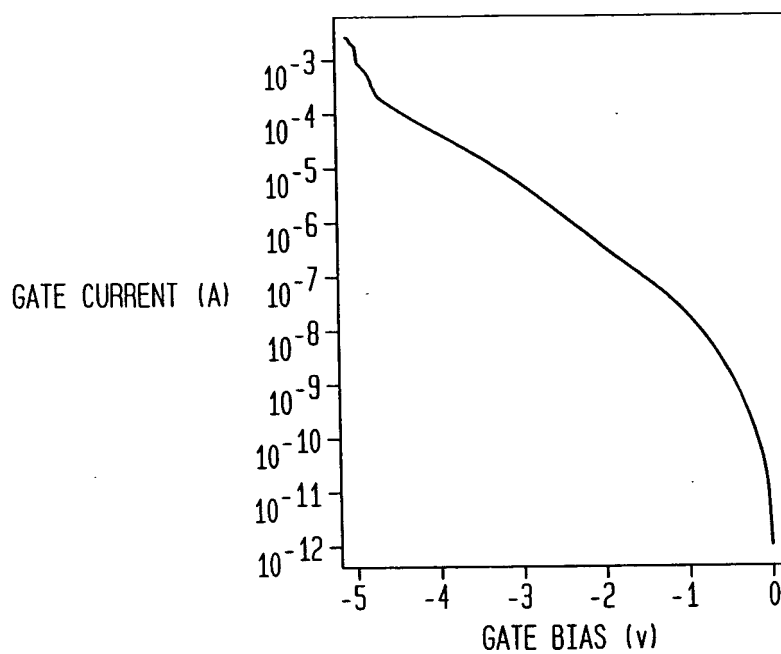
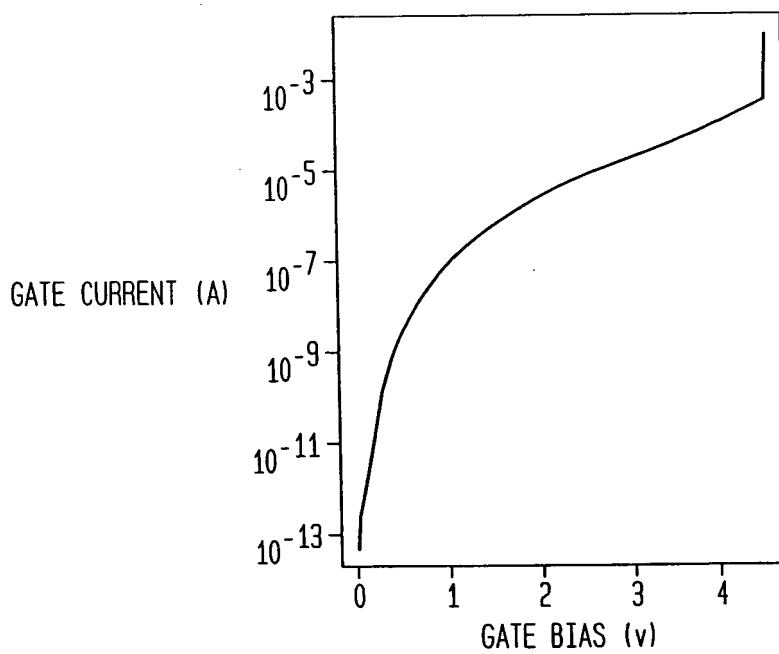
FIG. 2



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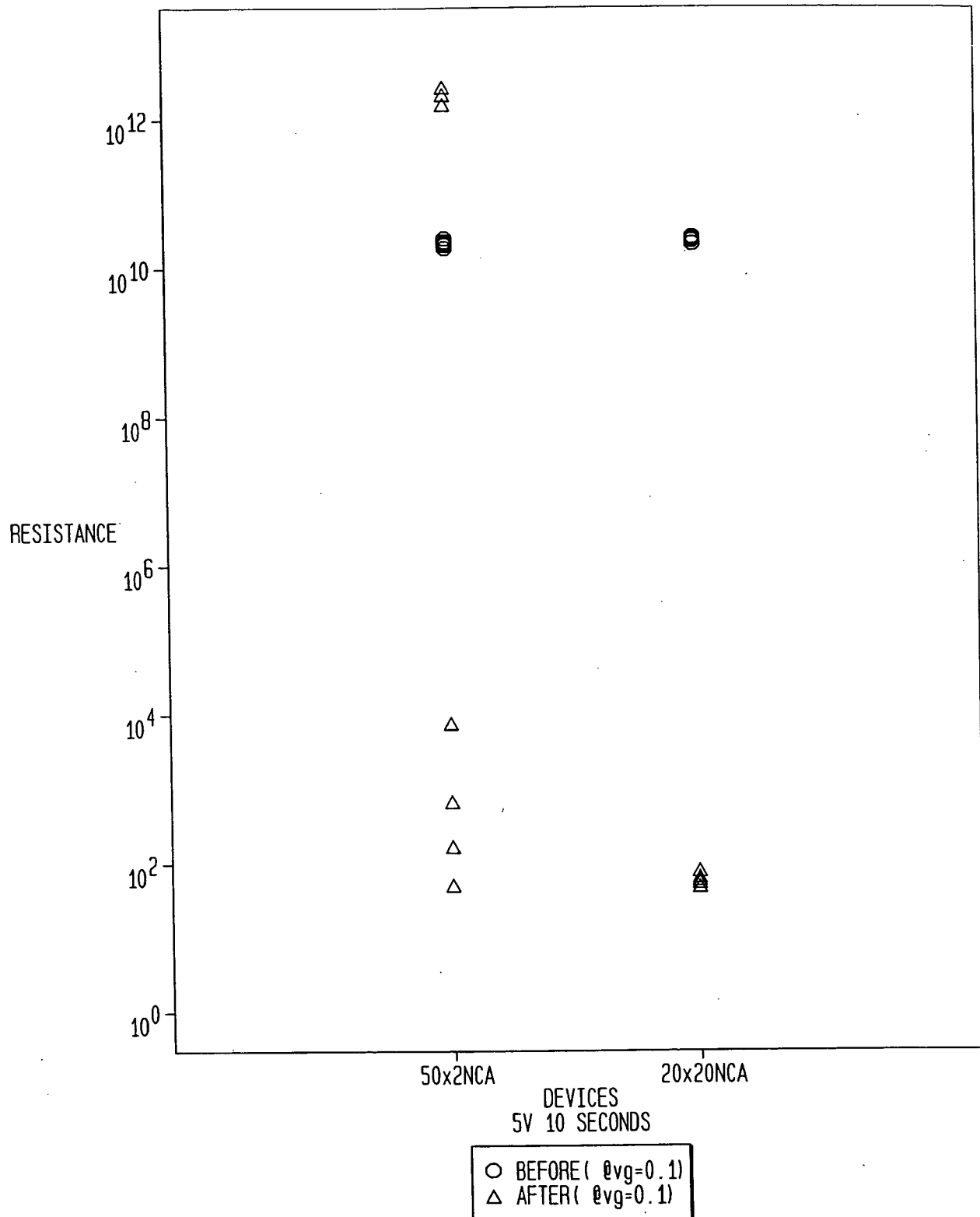


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FIG. 5ANMOS FET $10 \times 10 \text{ } \mu\text{m}^2$ S/D FLOAT**FIG. 5B**NMOS FET $10 \times 10 \text{ } \mu\text{m}^2$ 

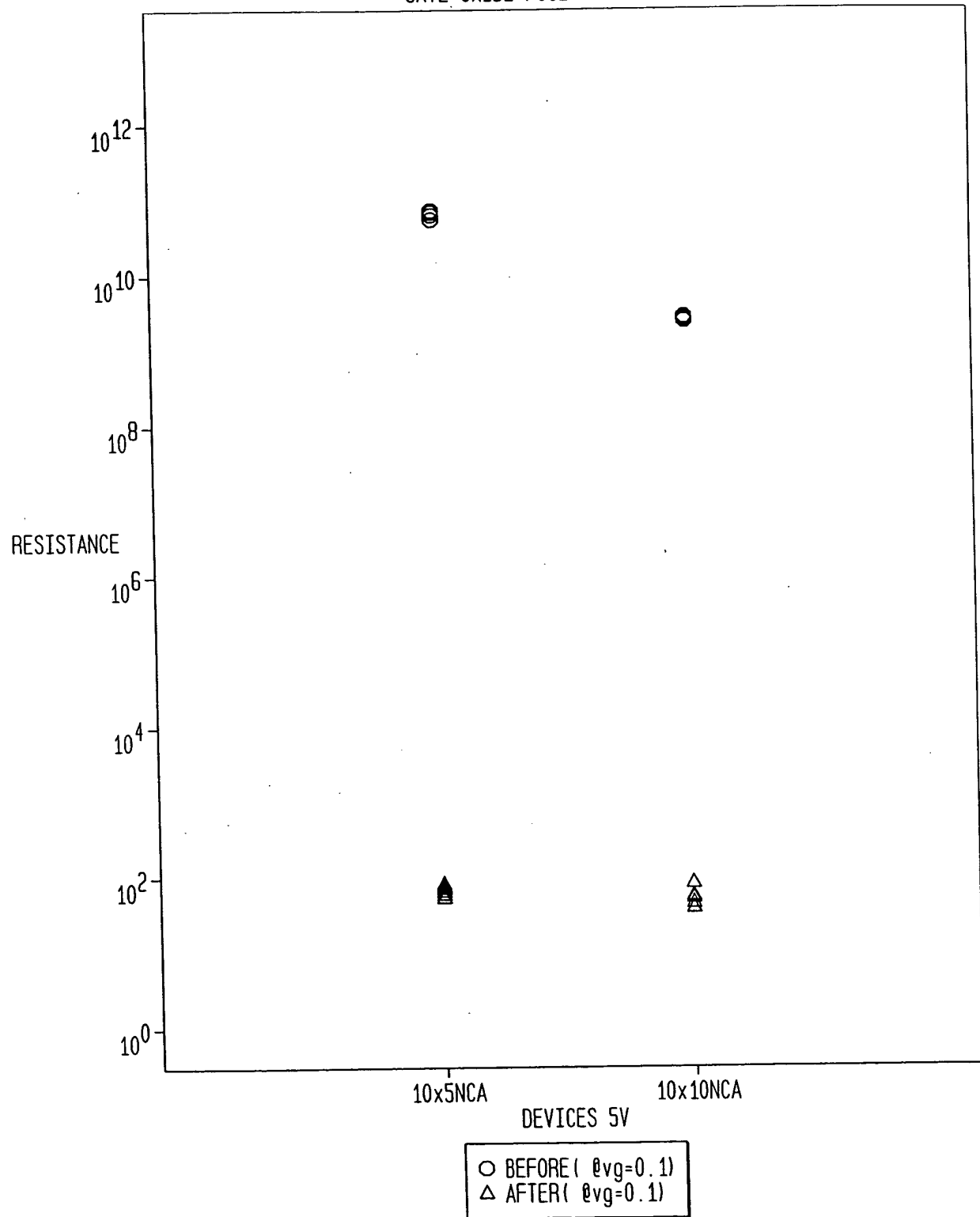
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FIG. 6A
GATE OXIDE FUSE



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FIG. 6B
GATE OXIDE FUSE



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FIG. 7

